

Title (en)
PHOTORECEPTOR CONSTRUCTION

Publication
EP 0049046 B1 19850403 (EN)

Application
EP 81303874 A 19810825

Priority
US 19042380 A 19800925

Abstract (en)
[origin: EP0049046A1] Thin photoconductive insulator layers are desirably used because of the reduced amount of materials necessary and their enhanced ability for light transmissivity. However, the thin construction tends to reduce the amount of charge that such a photoconductive layer can support. The use of a combined porous (14) and non-porous (18) barrier/charge transport layer below said photoconductive insulator layer (20) enables higher levels of charging in a photoconductive construction.

IPC 1-7
G03G 5/00

IPC 8 full level
G03G 5/08 (2006.01); **G03G 5/00** (2006.01); **G03G 5/047** (2006.01); **G03G 5/14** (2006.01)

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